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STH180N10F3-2

N-channel 100 V, 3.9 mΩ typ., 180 A, STripFET™ F3
 Power MOSFET in H²PAK-2 package

Datasheet - production data

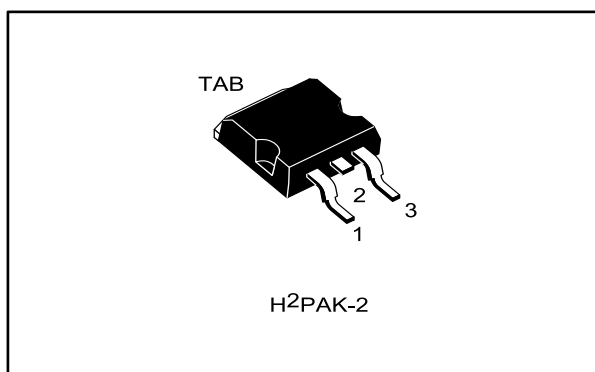
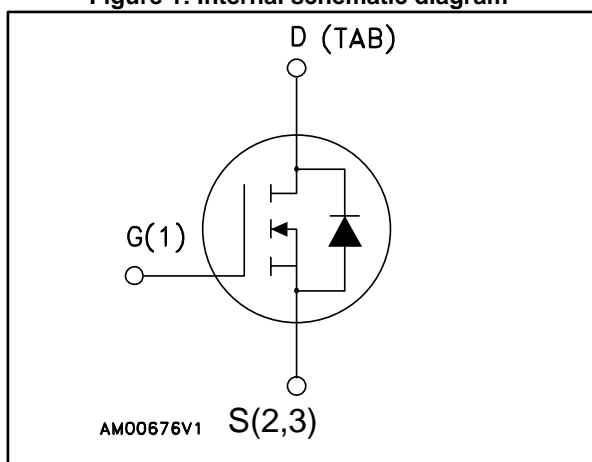


Figure 1: Internal schematic diagram



Features

| Order code | V _{DS} | R _{DS(on)} max. | I _D |
|---------------|-----------------|--------------------------|----------------|
| STH180N10F3-2 | 100 V | 4.5 mΩ | 180 A |

- Ultra low on-resistance
- 100% avalanche tested

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using STripFET™ F3 technology. It is designed to minimize on-resistance and gate charge to provide superior switching performance.

Table 1: Device summary

| Order code | Marking | Package | Packing |
|---------------|----------|----------------------|---------------|
| STH180N10F3-2 | 180N10F3 | H ² PAK-2 | Tape and reel |

Contents

| | | |
|----------|---|-----------|
| 1 | Electrical ratings | 3 |
| 2 | Electrical characteristics | 4 |
| | 2.1 Electrical characteristics (curves)..... | 6 |
| 3 | Test circuits | 8 |
| 4 | Package information | 9 |
| | 4.1 H ² PAK-2 package information..... | 10 |
| | 4.2 Packing information..... | 13 |
| 5 | Revision history | 15 |

1 Electrical ratings

Table 2: Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|---|------------|---------------------|
| V_{DS} | Drain-source voltage | 100 | V |
| V_{GS} | Gate-source voltage | ± 20 | V |
| $I_D^{(1)}$ | Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$ | 180 | A |
| $I_D^{(1)}$ | Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$ | 120 | A |
| $I_{DM}^{(2)}$ | Drain current (pulsed) | 720 | A |
| P_{TOT} | Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ | 315 | W |
| | Derating factor | 2.1 | W/ $^\circ\text{C}$ |
| dv/dt | Peak diode recovery voltage slope | 20 | V/ns |
| $E_{AS}^{(3)}$ | Single pulse avalanche energy | 350 | mJ |
| T_J | Operating junction temperature | -55 to 175 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | | $^\circ\text{C}$ |

Notes:

- ⁽¹⁾Current limited by package
- ⁽²⁾Pulse width limited by safe operating area
- ⁽³⁾Starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = 80$, $V_{DD} = 50\text{ V}$

Table 3: Thermal data

| Symbol | Parameter | Value | Unit |
|---------------------|----------------------------------|-------|--------------------|
| $R_{thj-case}$ | Thermal resistance junction-case | 0.48 | $^\circ\text{C/W}$ |
| $R_{thj-pcb}^{(1)}$ | Thermal resistance junction-pcb | 35 | $^\circ\text{C/W}$ |

Notes:

- ⁽¹⁾When mounted on FR-4 board of 1 inch², 2 oz Cu

Electrical characteristics

STH180N10F3-2

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4: On/off-state

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|----------------------|---|---|------|------|------|------|
| V _{(BR)DSS} | Drain-source breakdown voltage (V _{GS} = 0) | I _D = 250 μA | 100 | | | V |
| I _{DSS} | Zero gate voltage drain current (V _{GS} = 0) | V _{DS} = 100 V | | | 10 | μA |
| | | V _{DS} = 100 V; T _C = 125 °C | | | 100 | μA |
| I _{GSS} | Gate body leakage current (V _{DS} = 0) | V _{GS} = ±20 V | | | ±200 | nA |
| V _{GS(th)} | Gate threshold voltage | V _{DS} = V _{GS} , I _D = 250 μA | 2 | | 4 | V |
| R _{DS(on)} | Static drain-source on-resistance | V _{GS} = 10 V, I _D = 60 A | | 3.9 | 4.5 | mΩ |

Table 5: Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-------------------|------------------------------|---|------|-------|------|------|
| C _{iss} | Input capacitance | V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0 | - | 6665 | - | pF |
| C _{oss} | Output capacitance | | | 786 | | pF |
| C _{riss} | Reverse transfer capacitance | | | 49 | | pF |
| Q _g | Total gate charge | V _{DD} = 50 V, I _D = 120 A | | 114.6 | | nC |
| Q _{gs} | Gate-source charge | V _{GS} = 10 V | | 38.8 | | nC |
| Q _{gd} | Gate-drain charge | See Figure 14: "Gate charge test circuit" | | 31.9 | | nC |

Table 6: Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------------|---------------------|--|------|------|------|------|
| t _{d(on)} | Turn-on delay time | V _{DD} = 50 V, I _D = 60 A, R _G = 4.7 Ω, V _{GS} = 10 V See Figure 13: "Switching times test circuit for resistive load" | - | 25.6 | - | ns |
| t _r | Rise time | | | 97.1 | | ns |
| t _{d(off)} | Turn-off delay time | | | 99.9 | | ns |
| t _f | Fall time | | | 6.9 | | ns |

STH180N10F3-2

Electrical characteristics

Table 7: Source-drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|-------------------------------|---|------|-------|------|------|
| I_{SD} | Source-drain current | | | | 180 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | | | 720 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 120\text{ A},$ $V_{GS} = 0$ | - | | 1.5 | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 120\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s},$ | | 83.4 | | ns |
| Q_{rr} | Reverse recovery charge | $V_{DD} = 80\text{ V},$ $T_j = 150\text{ }^\circ\text{C}$ | | 295.7 | | nC |
| I_{RRM} | Reverse recovery current | | | 7.1 | | A |

Notes:

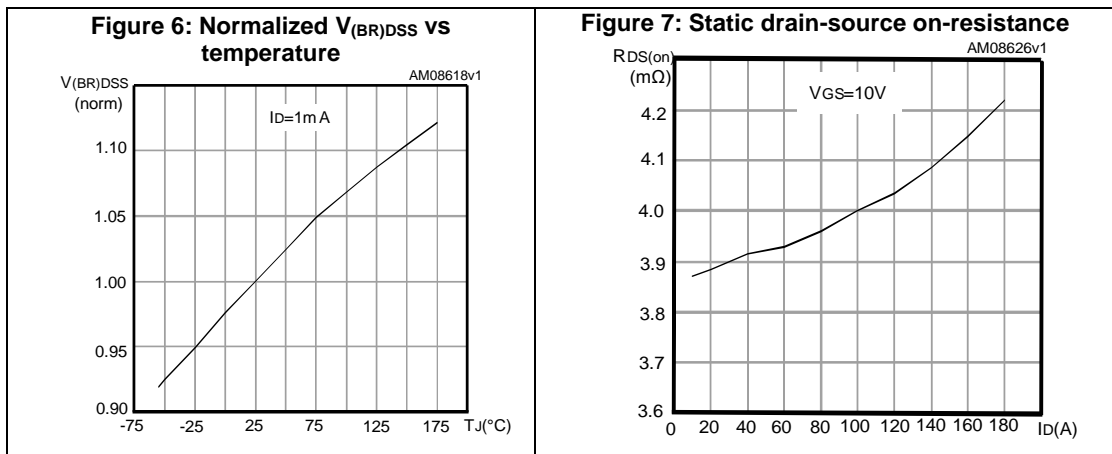
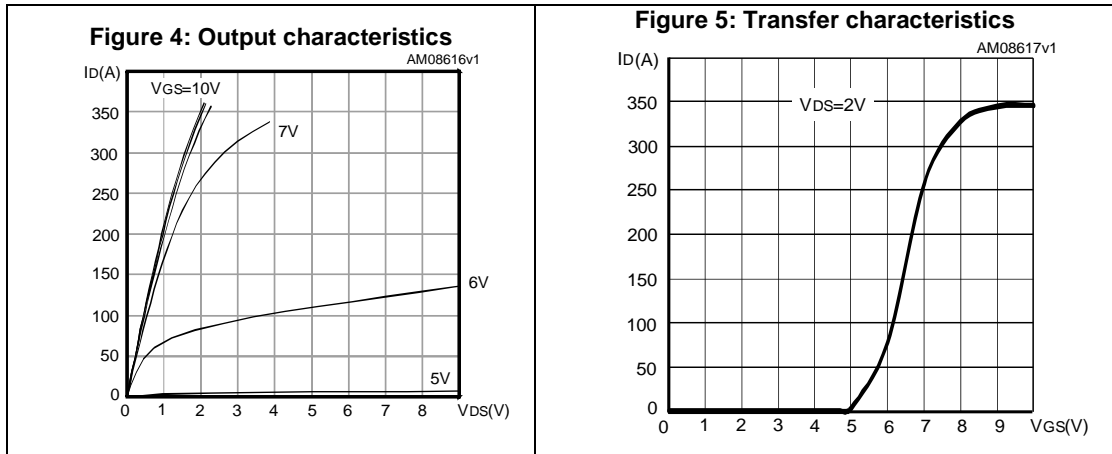
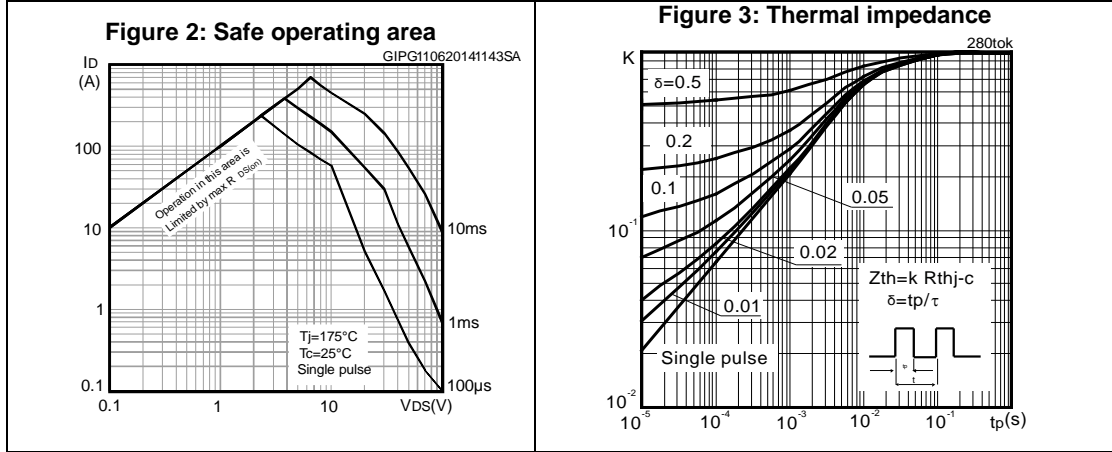
⁽¹⁾Pulse width limited by safe operating area

⁽²⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Electrical characteristics

STH180N10F3-2

2.1 Electrical characteristics (curves)



STH180N10F3-2

Electrical characteristics

Figure 8: Gate charge vs gate-source voltage

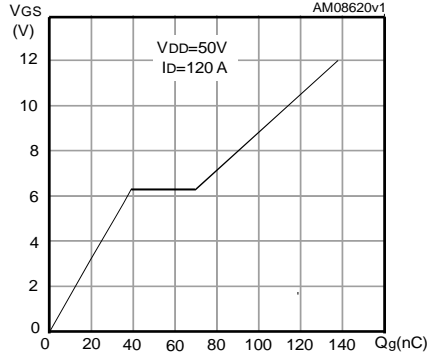


Figure 9: Capacitance variations

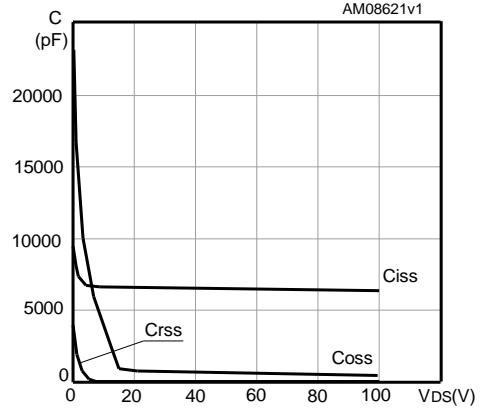


Figure 10: Normalized gate threshold voltage vs temperature

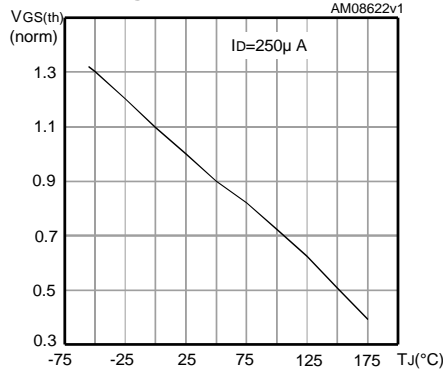


Figure 11: Normalized on-resistance vs temperature

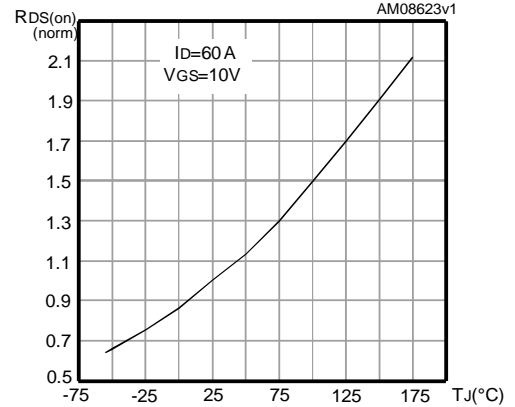
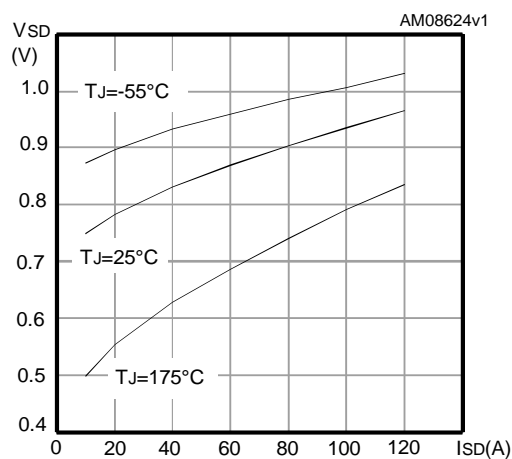


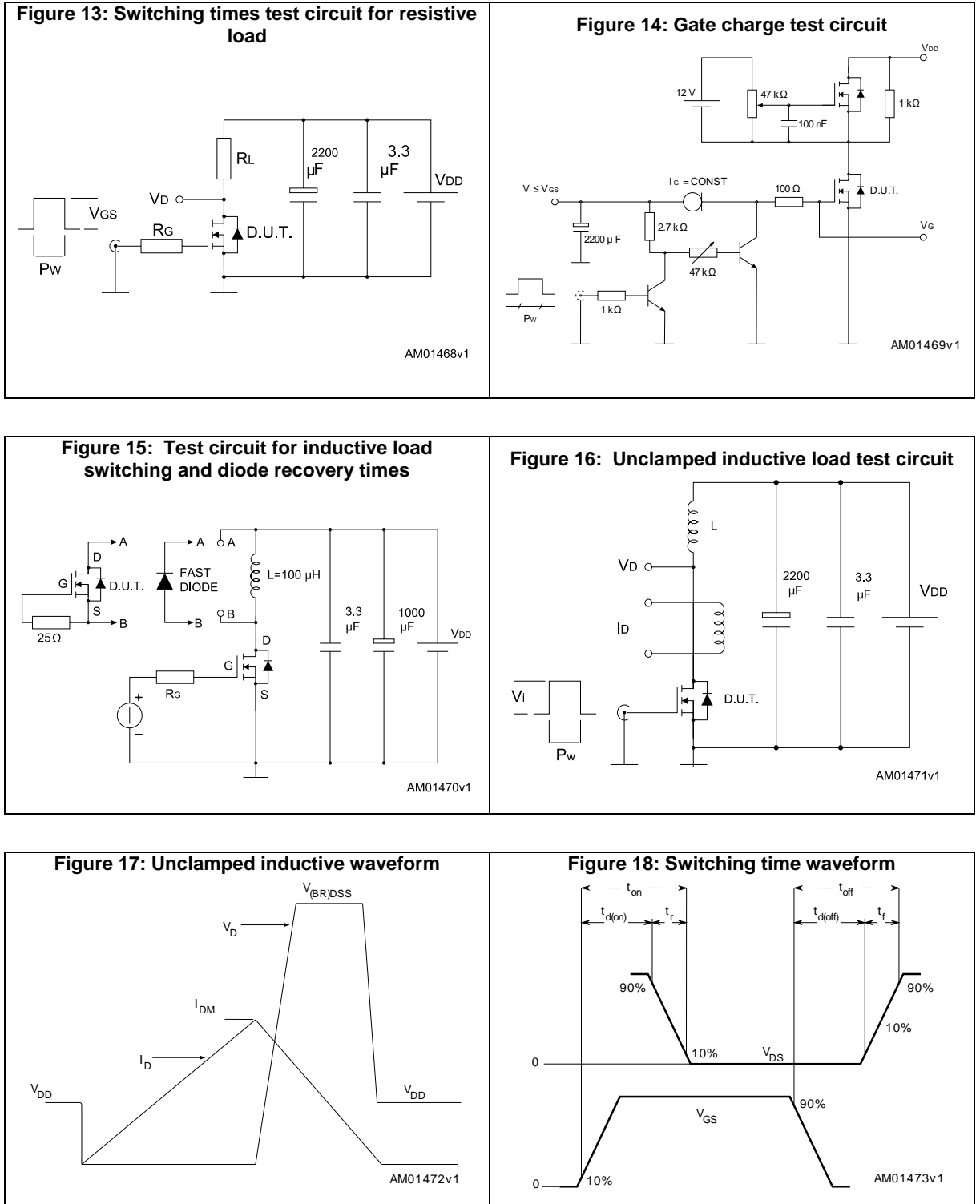
Figure 12: Source-drain diode forward characteristics



Test circuits

STH180N10F3-2

3 Test circuits



4 Package information

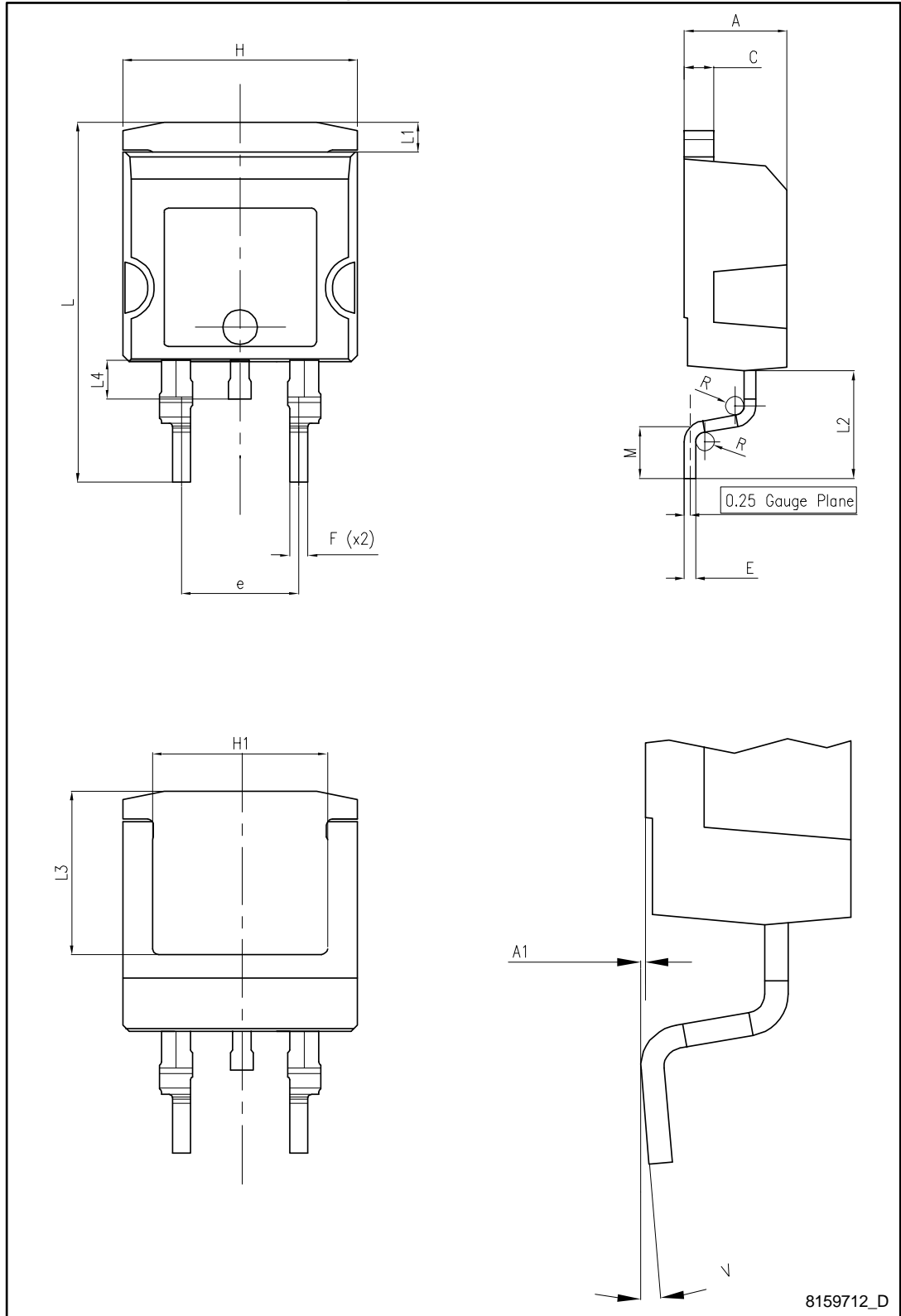
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Package information

STH180N10F3-2

4.1 H²PAK-2 package information

Figure 19: H²PAK-2 outline



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STH180N10F3-2

Package information

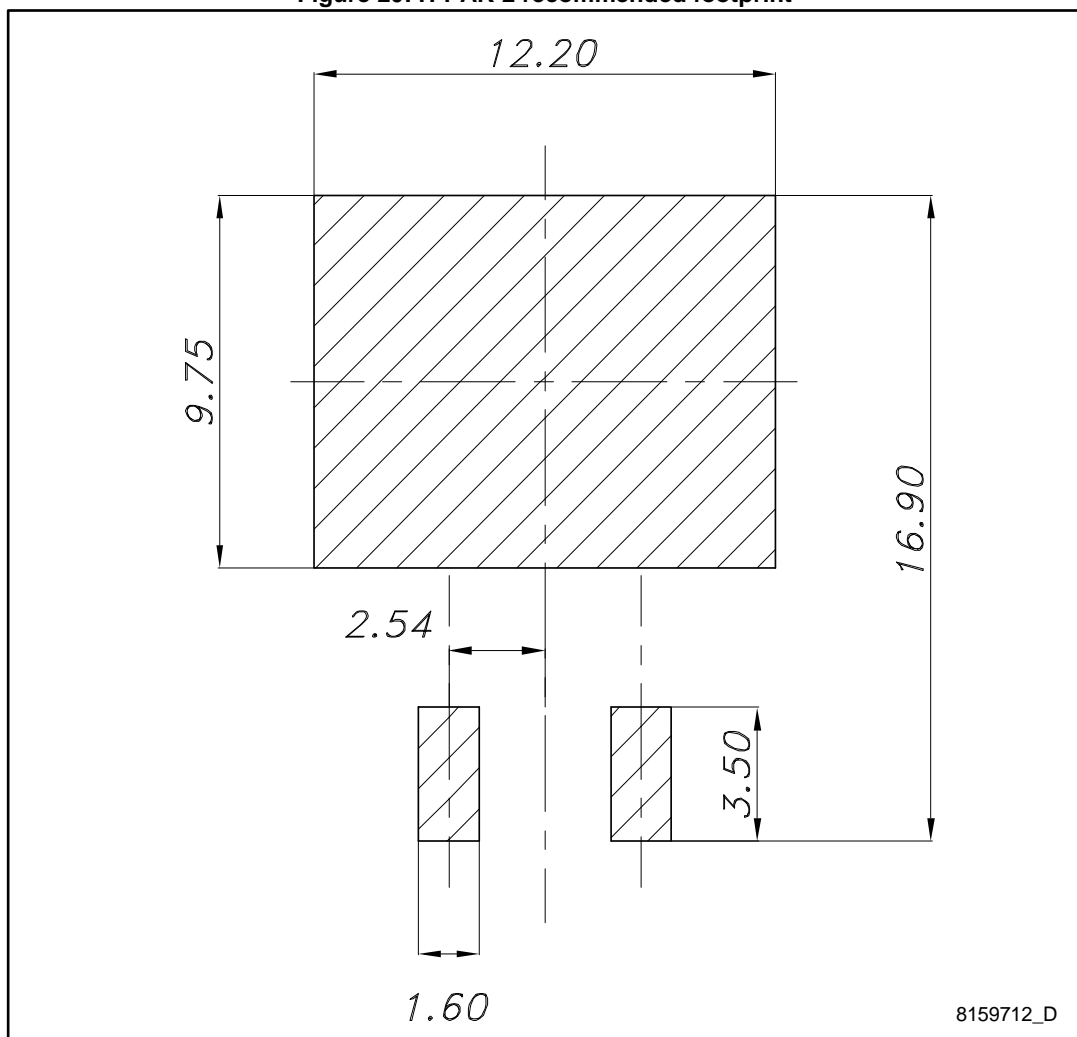
Table 8: H²PAK-2 mechanical data

| Dim. | mm | | |
|------|-------|------|-------|
| | Min. | Typ. | Max. |
| A | 4.30 | | 4.80 |
| A1 | 0.03 | | 0.20 |
| C | 1.17 | | 1.37 |
| e | 4.98 | | 5.18 |
| E | 0.50 | | 0.90 |
| F | 0.78 | | 0.85 |
| H | 10.00 | | 10.40 |
| H1 | 7.40 | | 7.80 |
| L | 15.30 | | 15.80 |
| L1 | 1.27 | | 1.40 |
| L2 | 4.93 | | 5.23 |
| L3 | 6.85 | | 7.25 |
| L4 | 1.5 | | 1.7 |
| M | 2.6 | | 2.9 |
| R | 0.20 | | 0.60 |
| V | 0° | | 8° |

Package information

STH180N10F3-2

Figure 20: H²PAK-2 recommended footprint



8159712_D

STH180N10F3-2

Package information

4.2 Packing information

Figure 21: Tape outline

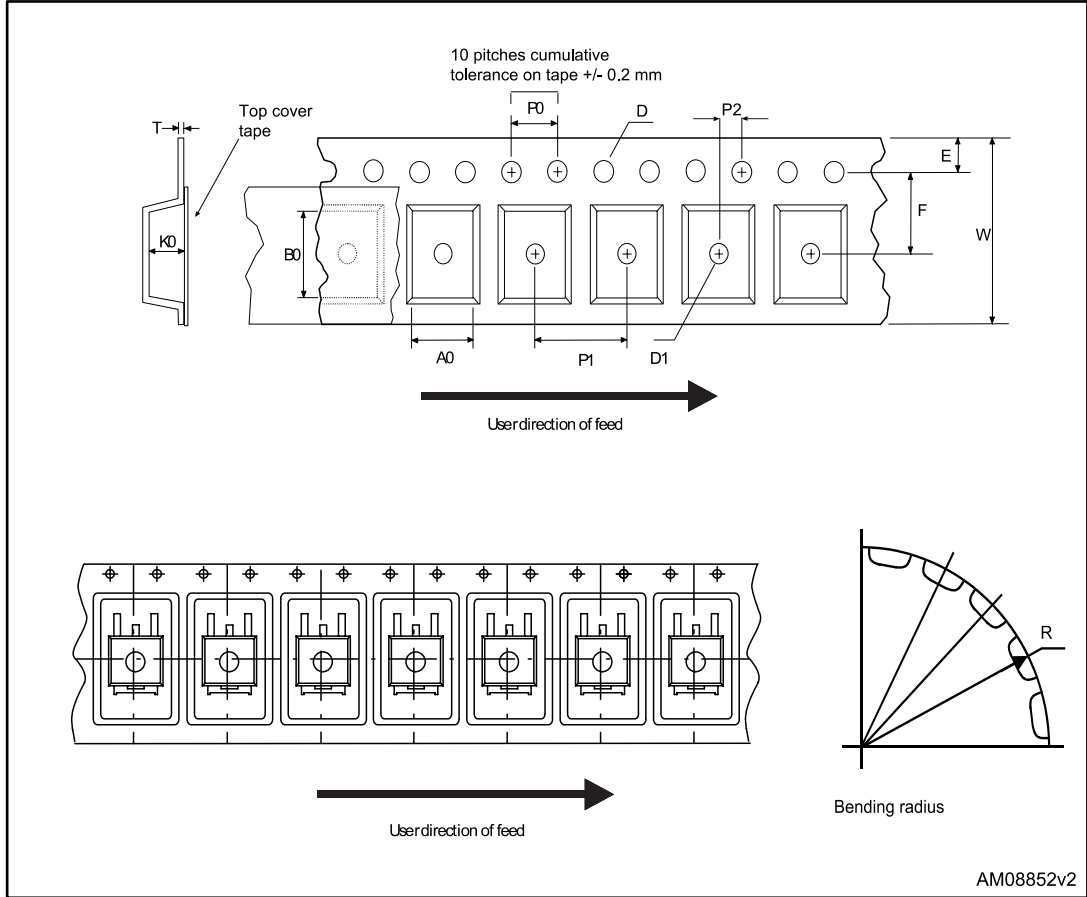
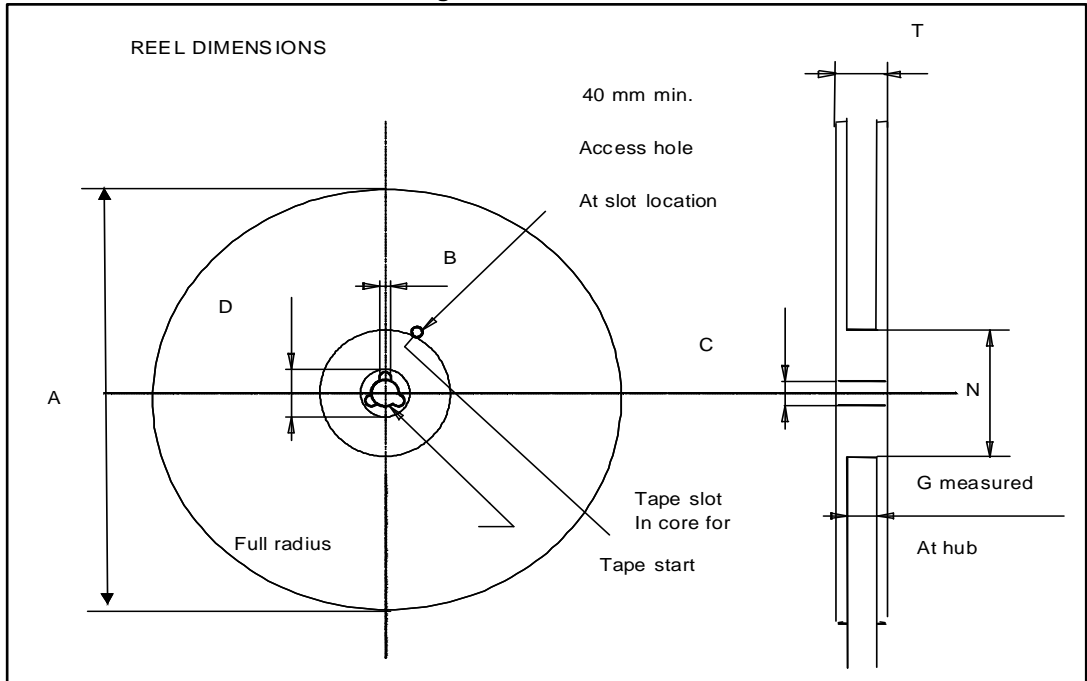


Figure 22: Reel outline



Package information

STH180N10F3-2

Table 9: Tape and reel mechanical data

| Tape | | | Reel | | |
|------|------|------|---------------|------|------|
| Dim. | mm | | Dim. | mm | |
| | Min. | Max. | | Min. | Max. |
| A0 | 10.5 | 10.7 | A | | 330 |
| B0 | 15.7 | 15.9 | B | 1.5 | |
| D | 1.5 | 1.6 | C | 12.8 | 13.2 |
| D1 | 1.59 | 1.61 | D | 20.2 | |
| E | 1.65 | 1.85 | G | 24.4 | 26.4 |
| F | 11.4 | 11.6 | N | 100 | |
| K0 | 4.8 | 5.0 | T | | 30.4 |
| P0 | 3.9 | 4.1 | | | |
| P1 | 11.9 | 12.1 | Base quantity | | 1000 |
| P2 | 1.9 | 2.1 | Bulk quantity | | 1000 |
| R | 50 | | | | |
| T | 0.25 | 0.35 | | | |
| W | 23.7 | 24.3 | | | |

5 Revision history

Table 10: Document revision history

| Date | Revision | Changes |
|-------------|----------|---|
| 18-Jul-2011 | 1 | First version |
| 26-Nov-2014 | 2 | <ul style="list-style-type: none">Modified fig 2.Updated package mechanical data.Updated the title, features and description. |

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